

BCR16KM-12LA

Triac

Medium Power Use

REJ03G0326-0100

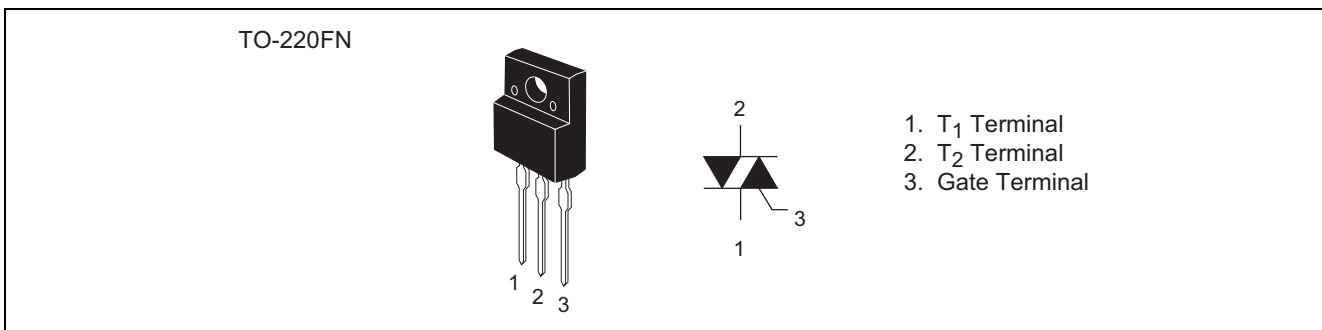
Rev.1.00

Aug.20.2004

Features

- $I_{T(RMS)}$: 16 A
- V_{DRM} : 600 V
- I_{FGTI} , I_{RGTI} , I_{RGTIII} : 30 mA (20 mA)^{Note5}
- V_{ISO} : 2000 V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904
File No. E80271

Outline



Applications

Switching mode power supply, washing machine, copying machine, motor control, heater control, and other general purpose control applications

Maximum Ratings

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Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I_T (RMS)	16	A	Commercial frequency, sine full wave 360° conduction, $T_c = 73^\circ\text{C}$
Surge on-state current	I_{TSM}	160	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	106.5	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	T_j	- 40 to +125	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +125	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	$T_a = 25^\circ\text{C}$, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied	
On-state voltage	V_{TM}	—	—	1.5	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 25\text{ A}$, Instantaneous measurement	
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	1.5	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	V_{RGTI}	—	—	1.5	V	
	III	V_{RGTIII}	—	—	1.5	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	30 ^{Note5}	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	I_{RGTI}	—	—	30 ^{Note5}	mA	
	III	I_{RGTIII}	—	—	30 ^{Note5}	mA	
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$	
Thermal resistance	$R_{th(j-c)}$	—	—	2.9	$^\circ\text{C}/\text{W}$	Junction to case ^{Note3}	
Critical-rate of rise of off-state commutating voltage ^{Note4}	$(dv/dt)_c$	10	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$	

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is $0.5^\circ\text{C}/\text{W}$.

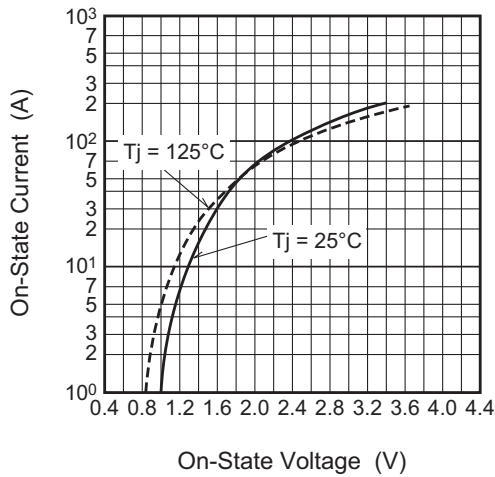
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

5. High sensitivity ($I_{GT} \leq 20\text{ mA}$) is also available. (I_{GT} item: 1)

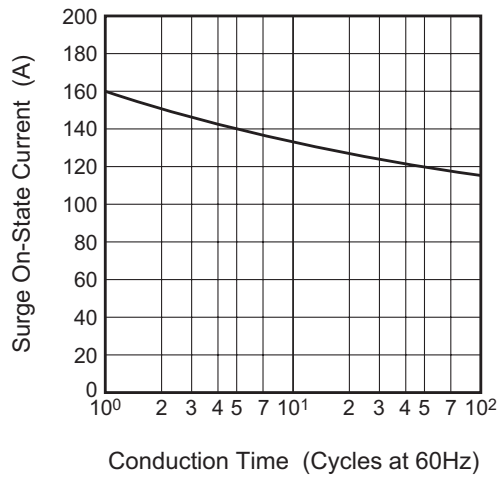
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -8\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

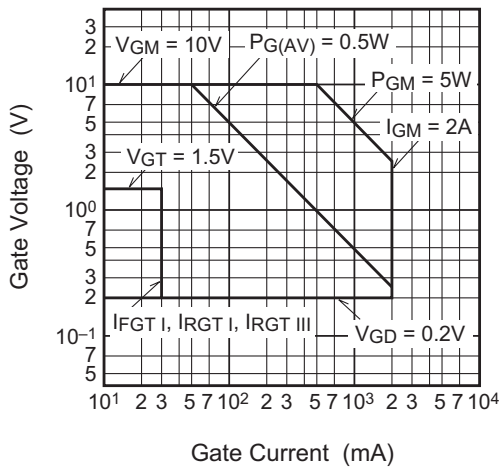
Maximum On-State Characteristics



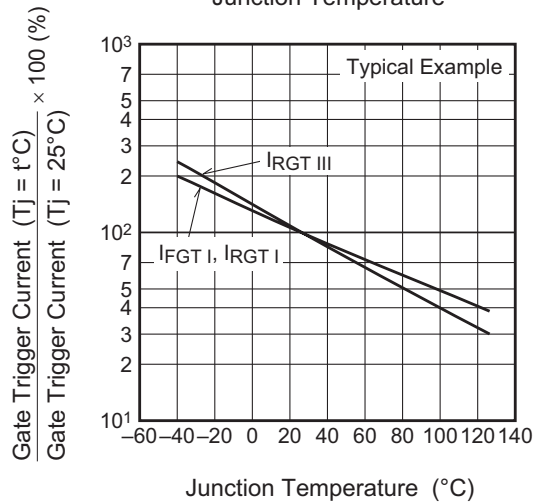
Rated Surge On-State Current



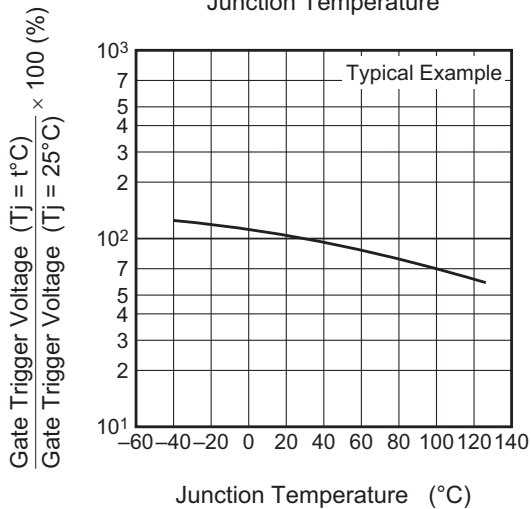
Gate Characteristics (I, II and III)



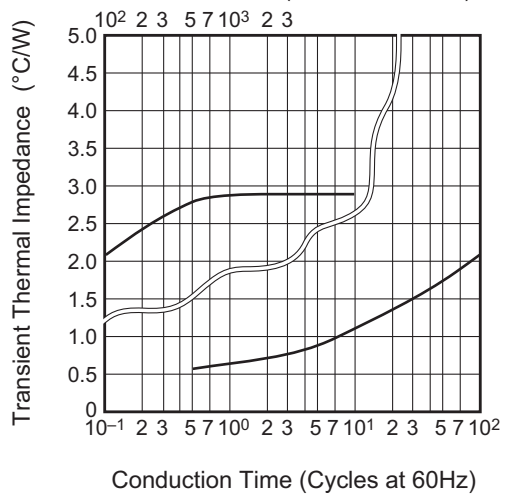
Gate Trigger Current vs. Junction Temperature



Gate Trigger Voltage vs. Junction Temperature

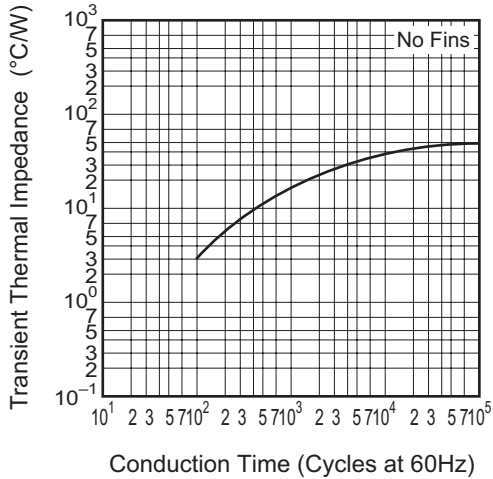


Maximum Transient Thermal Impedance Characteristics (Junction to case)

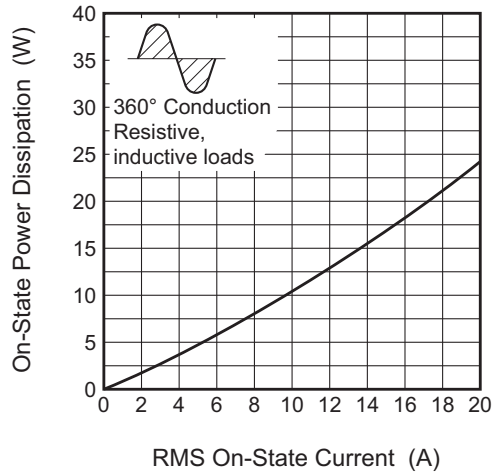


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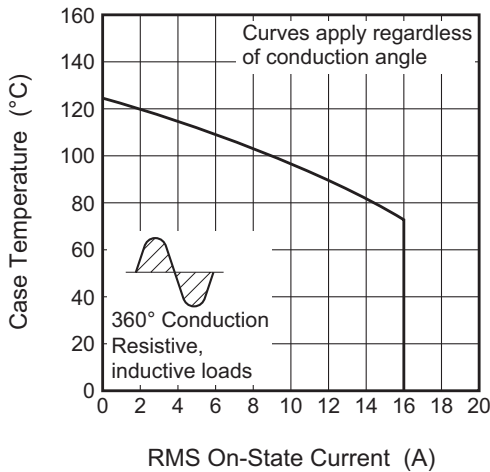
Maximum Transient Thermal Impedance Characteristics (Junction to ambient)



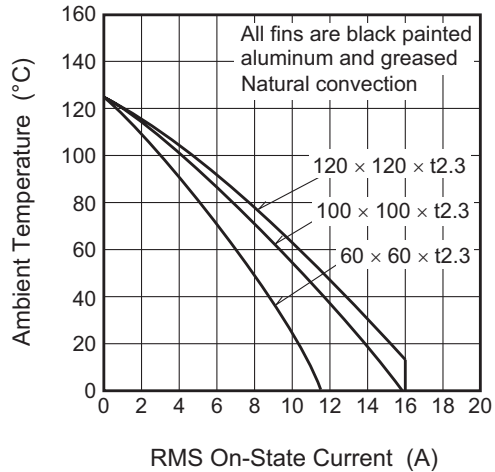
Maximum On-State Power Dissipation



Allowable Case Temperature vs. RMS On-State Current

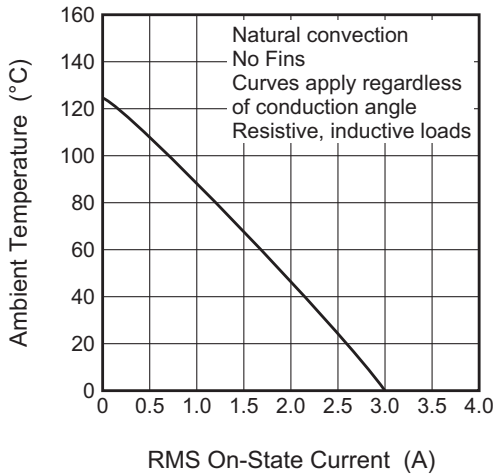


Allowable Ambient Temperature vs. RMS On-State Current

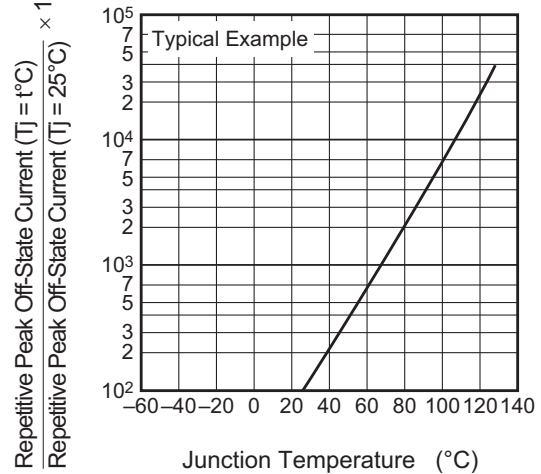


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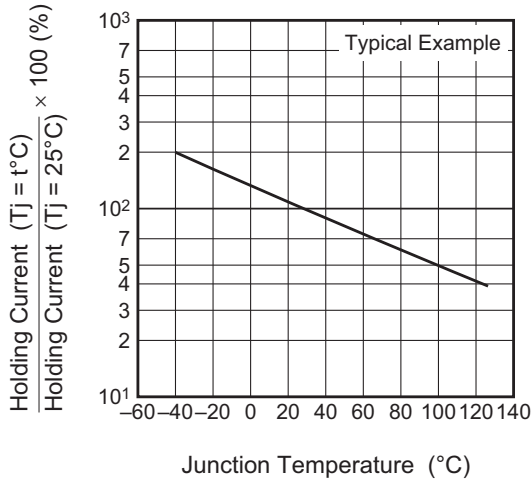
Allowable Ambient Temperature vs. RMS On-State Current



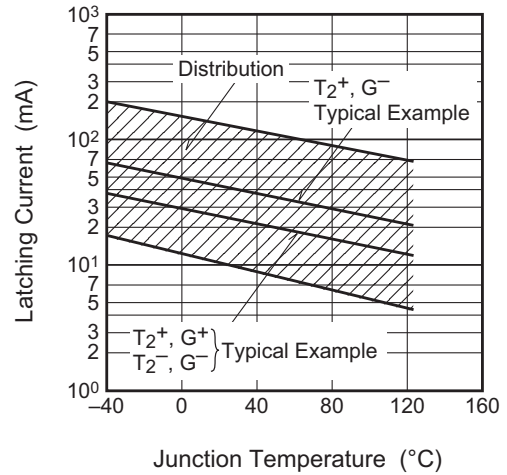
Repetitive Peak Off-State Current vs. Junction Temperature



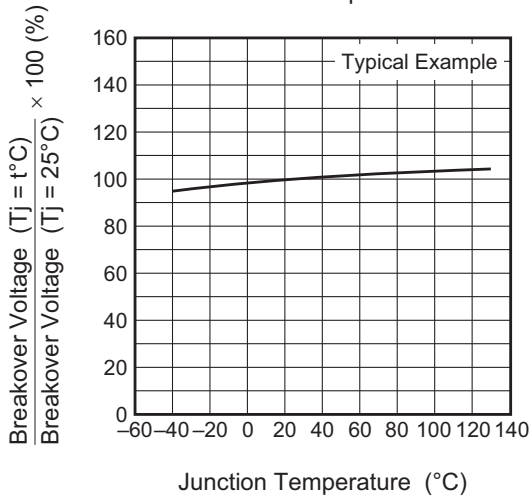
Holding Current vs. Junction Temperature



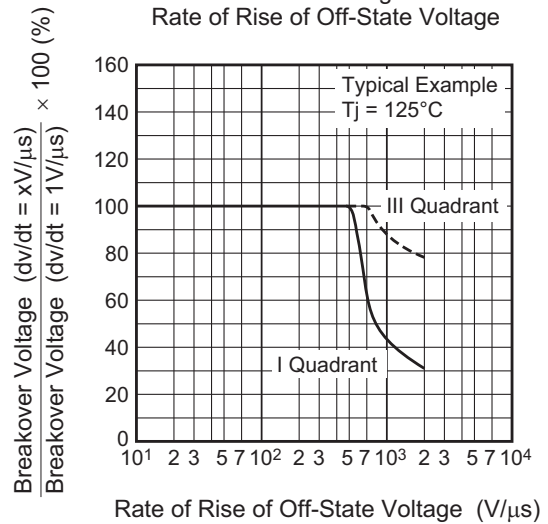
Latching Current vs. Junction Temperature



Breakover Voltage vs. Junction Temperature

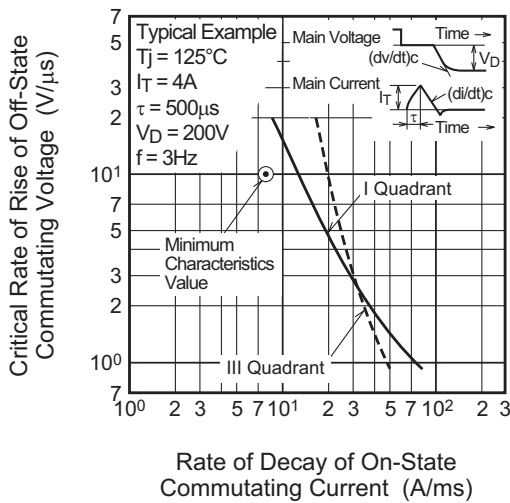


Breakover Voltage vs. Rate of Rise of Off-State Voltage

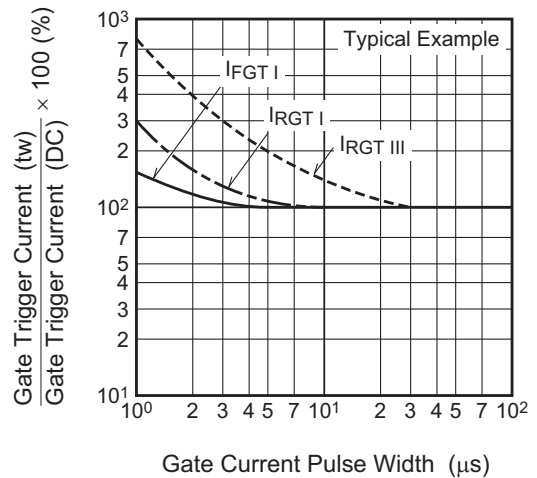


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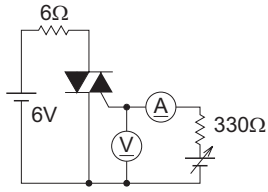
Commutation Characteristics



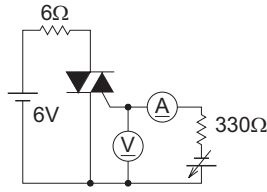
Gate Trigger Current vs. Gate Current Pulse Width



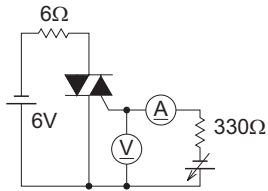
Gate Trigger Characteristics Test Circuits



Test Procedure I



Test Procedure II



Test Procedure III

Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy

Technical drawings showing dimensions for the TO-220FN package. Dimensions include: 10 ± 0.3, 3 ± 0.3, 15 ± 0.3, 6.5 ± 0.3, φ 3.2 ± 0.2, 14 ± 0.5, 3.6 ± 0.3, 1.1 ± 0.2, 0.75 ± 0.15, 2.54 ± 0.25, 2.8 ± 0.2, 0.75 ± 0.15, 4.5 ± 0.2, and 2.6 ± 0.2.

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	BCR16KM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR16KM-12LA-A8

Note : Please confirm the specification about the shipping in detail.

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